NSN 5962-01-174-1380

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-174-1380

Body Length: 1.060 inches **Body Width:** Between 0.220 inches and 0.310 inches **Body Height:** 0.185 inches **Maximum Power Dissipation Rating:** 2.0 watts **Operating Tempurature Range:** -55.0/+125.0 degrees celsius Storage Tempurature Range: -65.0/+150.0 degrees celsius **Features Provided:** Hermetically sealed and burn in and monolithic and programmable and bipolar **Inclosure Material:** Ceramic **Inclosure Configuration:** Dual-in-line **Output Logic Form:** Bipolar metal-oxide semiconductor **Input Circuit Pattern:** 16 input **Case Outline Source And Designator:** D-8 mil-m-38510 **Current Rating Per Characteristic:** 100.00 milliamperes reverse current, dc **Terminal Surface Treatment:** Solder Voltage Rating And Type Per Characteristic: 5.0 volts power source **Time Rating Per Chacteristic:** 45.00 nanoseconds propagation delay time, low to high level output and 45.00 nanoseconds propagation delay time, high to low level output Memory Device Type: Pal **Test Data Document:** 81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:**

20 printed circuit

Specification Data:

81349-mil-m-38510/503 government specification

Shelf Life:

NI/o

NSN 5962-01-174-1380

Memory Microcircuit - Page 2 of 2

Unit Of Measure:

Demilitarization:

No

Fiig:

A458a0

